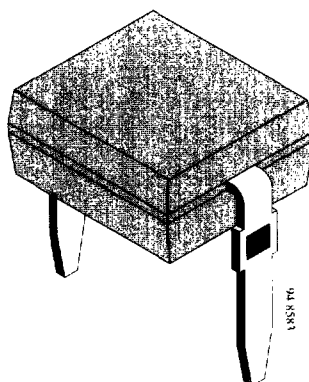


Silicon PIN Photodiode

Description

The BPW34 is a high speed and high sensitive PIN photodiode in a miniature flat plastic package. Its top view construction makes it ideal as a low cost replacement of TO-5 devices in many applications.

Due to its waterclear epoxy the device is sensitive to visible and infrared radiation. The large active area combined with a flat case gives a high sensitivity at a wide viewing angle.



Features

- Large radiant sensitive area ($A=7.5 \text{ mm}^2$)
- Wide angle of half sensitivity $\phi = \pm 65^\circ$
- High photo sensitivity
- Fast response times
- Small junction capacitance
- Suitable for visible and near infrared radiation

Applications

High speed photo detector

Absolute Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Reverse Voltage		V_R	60	V
Power Dissipation	$T_{\text{amb}} \leq 25^\circ\text{C}$	P_V	215	mW
Junction Temperature		T_j	100	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	$-55 \dots +100$	$^\circ\text{C}$
Soldering Temperature	$t \leq 3 \text{ s}$	T_{sd}	260	$^\circ\text{C}$
Thermal Resistance Junction/Ambient		R_{thJA}	350	K/W

Basic Characteristics

$T_{amb} = 25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Breakdown Voltage	$I_R = 100\text{ }\mu\text{A}$, $E = 0$	$V_{(BR)}$	60			V
Reverse Dark Current	$V_R = 10\text{ V}$, $E = 0$	I_{ro}		2	30	nA
Diode Capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_D		70		pF
	$V_R = 3\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_D		25	40	pF
Open Circuit Voltage	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	V_o		350		mV
Temp. Coefficient of V_o	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	TK_{V_o}		-2.6		mV/K
Short Circuit Current	$E_A = 1\text{ klx}$	I_k		70		μA
	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	I_k		47		μA
Temp. Coefficient of I_k	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$	TK_{I_k}		0.1		%/K
Reverse Light Current	$E_A = 1\text{ klx}$, $V_R = 5\text{ V}$	I_{ra}		75		μA
	$E_e = 1\text{ mW/cm}^2$, $\lambda = 950\text{ nm}$, $V_R = 5\text{ V}$	I_{ra}	40	50		μA
Angle of Half Sensitivity		φ		± 65		deg
Wavelength of Peak Sensitivity		λ_p		900		nm
Range of Spectral Bandwidth		$\lambda_{0.5}$		600...1050		nm
Noise Equivalent Power	$V_R = 10\text{ V}$, $\lambda = 950\text{ nm}$	NEP		4×10^{-14}		W/ $\sqrt{\text{Hz}}$
Rise Time	$V_R = 10\text{ V}$, $R_L = 1\text{ k}\Omega$, $\lambda = 820\text{ nm}$	t_r		100		ns
Fall Time	$V_R = 10\text{ V}$, $R_L = 1\text{ k}\Omega$, $\lambda = 820\text{ nm}$	t_f		100		ns

Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)

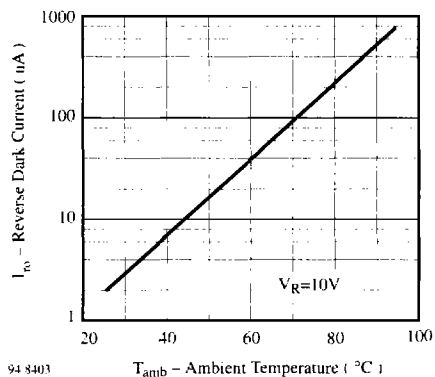


Figure 1. Reverse Dark Current vs. Ambient Temperature

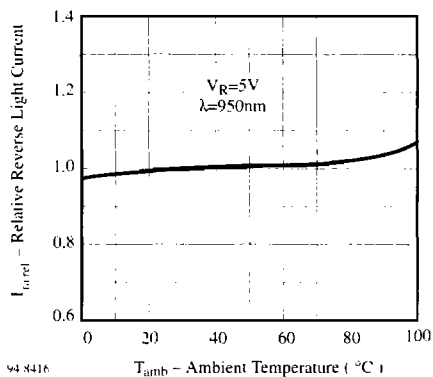


Figure 2. Relative Reverse Light Current vs. Ambient Temperature

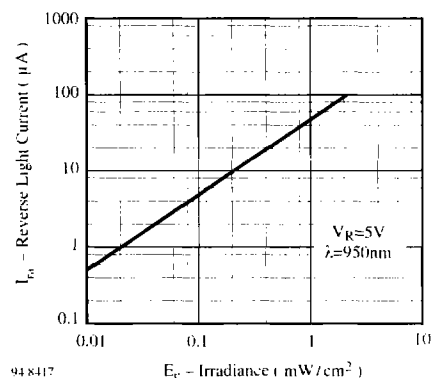


Figure 3. Reverse Light Current vs. Irradiance

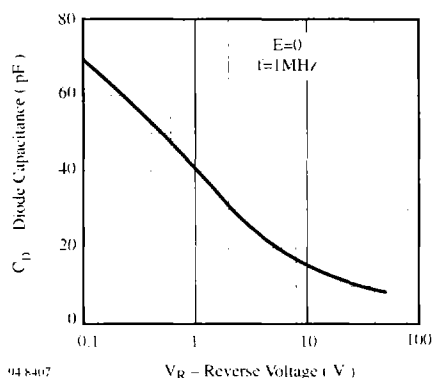


Figure 6. Diode Capacitance vs. Reverse Voltage

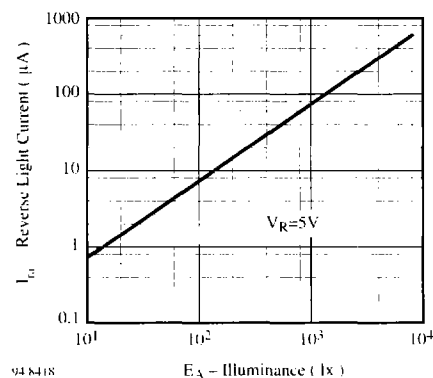


Figure 4. Reverse Light Current vs. Illuminance

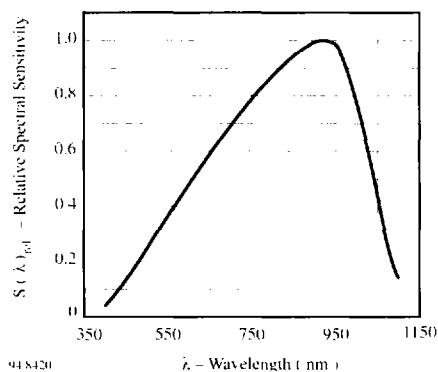


Figure 7. Relative Spectral Sensitivity vs. Wavelength

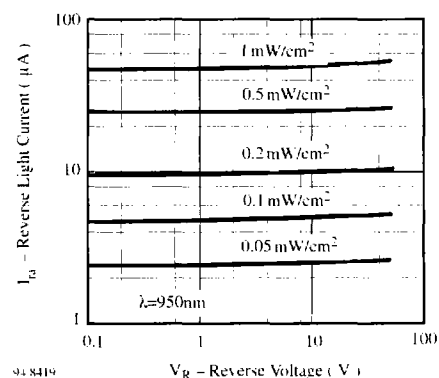


Figure 5. Reverse Light Current vs. Reverse Voltage

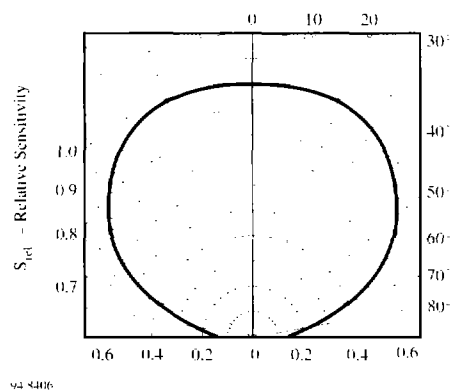


Figure 8. Relative Radiant Sensitivity vs. Angular Displacement

Dimensions in mm

